Title (en)

PROCESS FOR FABRICATING A SILICON-BASED THIN-FILM PHOTOVOLTAIC CELL

Title (de)

VERFAHREN ZUR HERSTELLUNG EINER PHOTOVOLTAISCHEN DÜNNSCHICHTZELLE AUF SILIZIUMBASIS

Title (fr)

PROCEDE DE FABRICATION D'UNE CELLULE PHOTOVOLTAÏQUE A BASE DE SILICIUM EN COUCHES MINCES

Publication

EP 2281313 A2 20110209 (FR)

Application

EP 09738349 A 20090420

Priority

- FR 2009000461 W 20090420
- FR 0802270 A 20080423

Abstract (en)

[origin: WO2009133315A2] The invention relates to a process for fabricating a silicon-based thin-film photovoltaic cell. This fabrication process is characterized in that it includes a step a) of depositing a p-doped or n-doped amorphous silicon film, the X-ray diffraction spectrum of which has a line centred at 28° that has a mid-height width, denoted by a, such that 4.7° = a < 6.0° on a substrate (1). The invention is applicable in particular in the energy generation field.

IPC 8 full level

H01L 31/0368 (2006.01); **H01L 31/04** (2006.01); **H01L 31/0745** (2012.01); **H01L 31/18** (2006.01); **H01L 31/20** (2006.01)

CPC (source: EP US)

H01L 31/03682 (2013.01 - EP US); **H01L 31/0745** (2013.01 - EP US); **H01L 31/182** (2013.01 - EP US); **H01L 31/1872** (2013.01 - EP US); **H01L 31/202** (2013.01 - EP US); Y02E 10/546 (2013.01 - EP US); Y02P 70/50 (2015.11 - EP US)

Citation (search report)

See references of WO 2009133315A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO SE SI SK TR

Designated extension state (EPC)

AL BA RS

DOCDB simple family (publication)

FR 2930680 A1 20091030; **FR 2930680 B1 20100827**; BR PI0911637 A2 20180327; EP 2281313 A2 20110209; JP 2011519158 A 20110630; KR 20100136554 A 20101228; US 2011223711 A1 20110915; US 8288196 B2 20121016; WO 2009133315 A2 20091105; WO 2009133315 A3 20101111

DOCDB simple family (application)

FR 0802270 A 20080423; BR PI0911637 A 20090420; EP 09738349 A 20090420; FR 2009000461 W 20090420; JP 2011505554 A 20090420; KR 20107026108 A 20090420; US 98931109 A 20090420